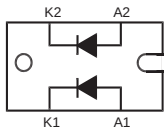
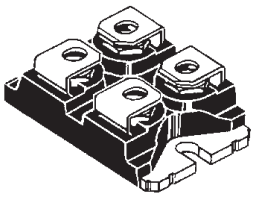
BYV255V

HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED :
  Insulating voltage = 2500 V_{RMS}
  Capacitance = 55 pF





ISOTOP
(Plastic)

DESCRIPTION

Dual rectifier suited for switchmode power supply and high frequency DC to DC converters.
Packaged in ISOTOP™ this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
$I_{F(RMS)}$	RMS forward current		Per diode	150	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	Tc=110°C	Per diode	100	A
I_{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	Per diode	1600	A
Tstg Tj	Storage and junction temperature range			- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V

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THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	Per diode	0.4	°C/W
		Total	0.25	
Rth (c)	Coupling		0.1	°C/W

When the diodes 1 and 2 are used simultaneously :
Tj-Tc (diode 1) = P(diode 1) x Rth(j-c)(Per diode) + P(diode 2) x Rth(c)

ELECTRICAL CHARACTERISTICS (Per diode)
STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R *	T_j = 25°C	$V_R = V_{RRM}$			100	µA
	T_j = 100°C				10	mA
V_F **	T_j = 125°C	I_F = 100 A			0.85	V
	T_j = 125°C	I_F = 200 A			1.00	
	T_j = 25°C	I_F = 200 A			1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %
** tp = 380 µs, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
trr	T_j = 25°C	I_F = 0.5A I_R = 1A	Irr = 0.25A			55	ns
		I_F = 1A V_R = 30V	dI_F/dt = -50A/µs			80	
tfr	T_j = 25°C	I_F = 1A $V_{FR} = 1.1 \times V_F$	tr = 5 ns		10		ns
V_{FP}	T_j = 25°C	I_F = 1A	tr = 5 ns		1.5		V

TURN-OFF SWITCHING CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
I_{RM}	T_j = 100°C	I_F = 100A Lp ® 0.05µH Vcc ® 0.6 V_{RRM}	dIF/dt = -200A/µs			16	A
			dI_F/dt = -400A/µs		24		

Fig.1 : Average forward power dissipation versus average forward current.

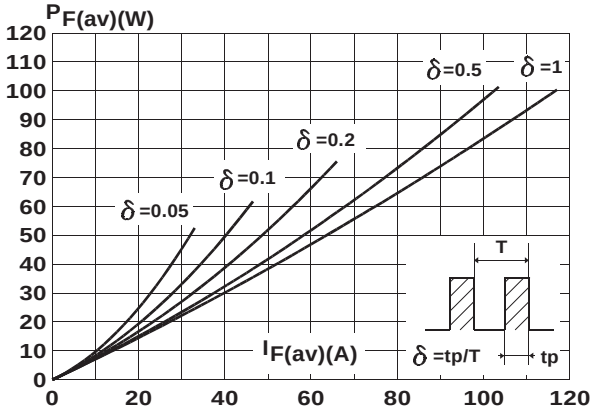


Fig.2 : Peak current versus form factor.

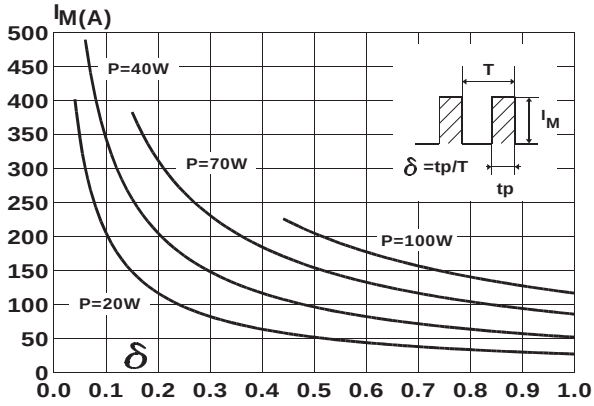


Fig.3 : Forward voltage drop versus forward current (maximum values).

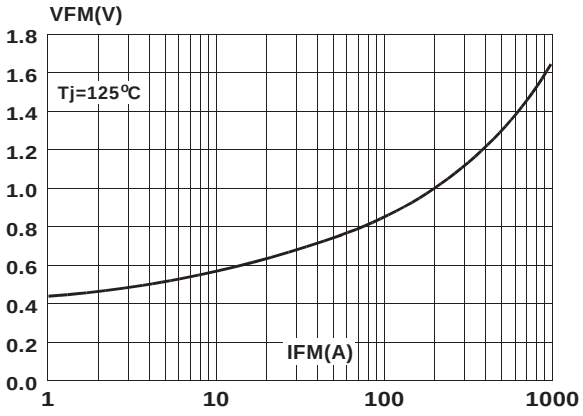


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

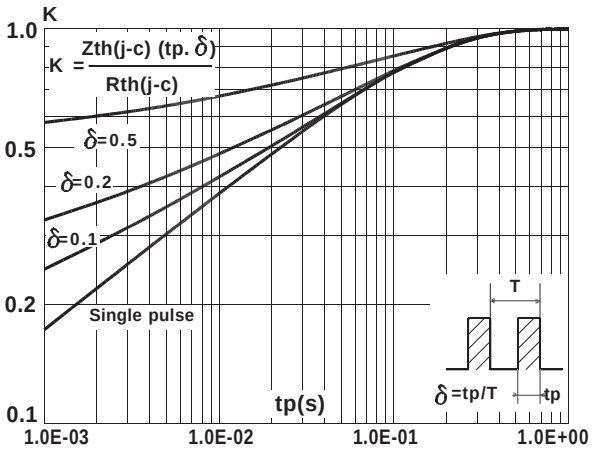


Fig.5 : Non repetitive surge peak forward current versus overload duration.

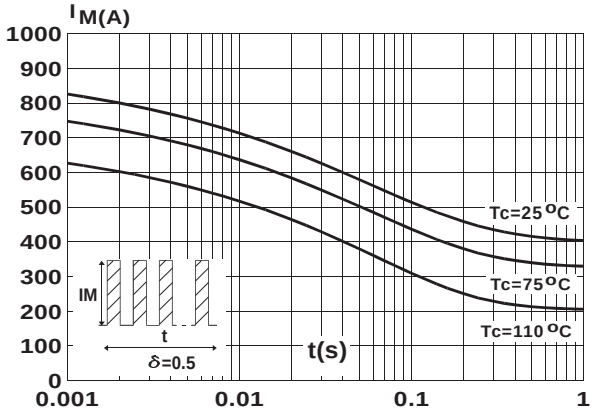


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)

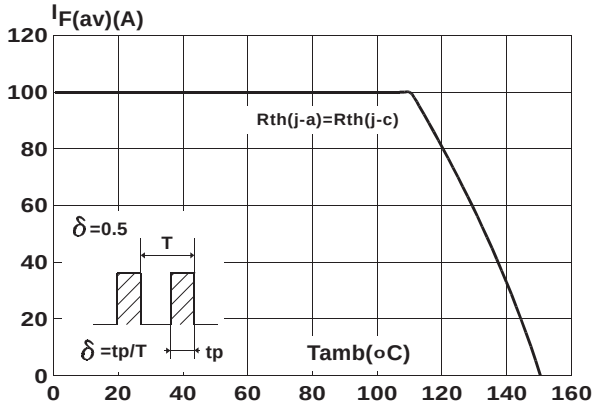


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

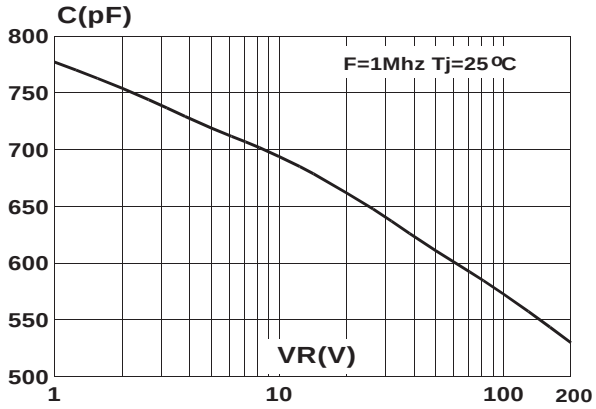


Fig.8 : Recovery charges versus dI_F/dt.

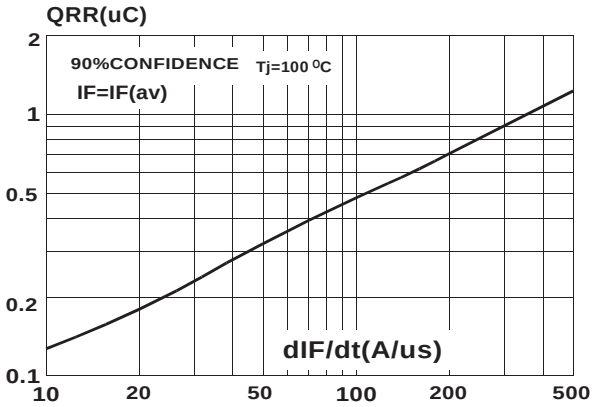


Fig.9 : Peak reverse current versus dIF/dt.

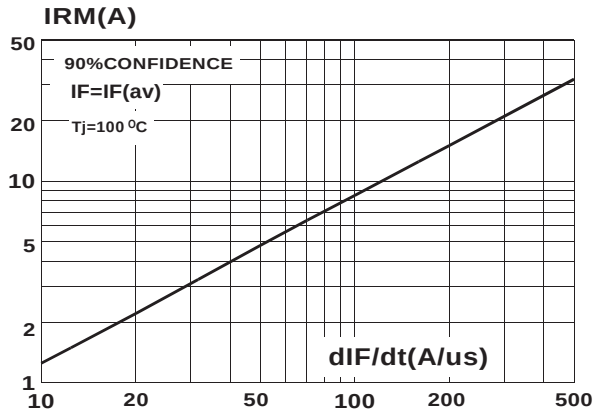
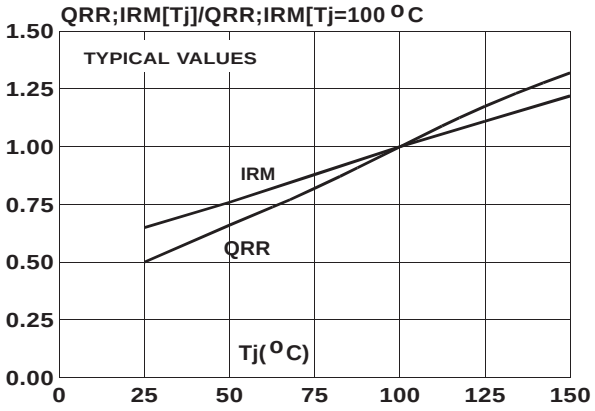
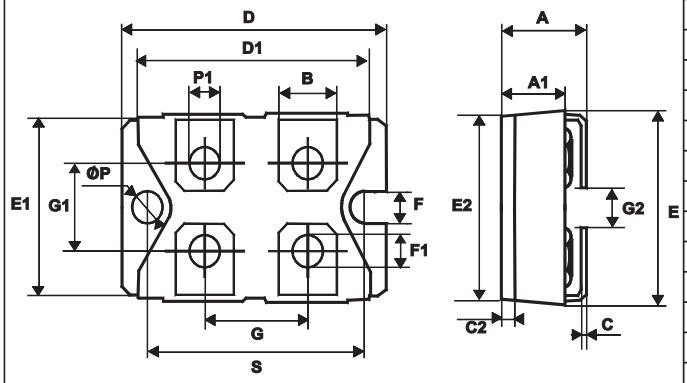


Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA

ISOTOP



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

- **Marking** : Type number
- Cooling method : C
- Weight : 27 g
- Epoxy meets UL94, V0